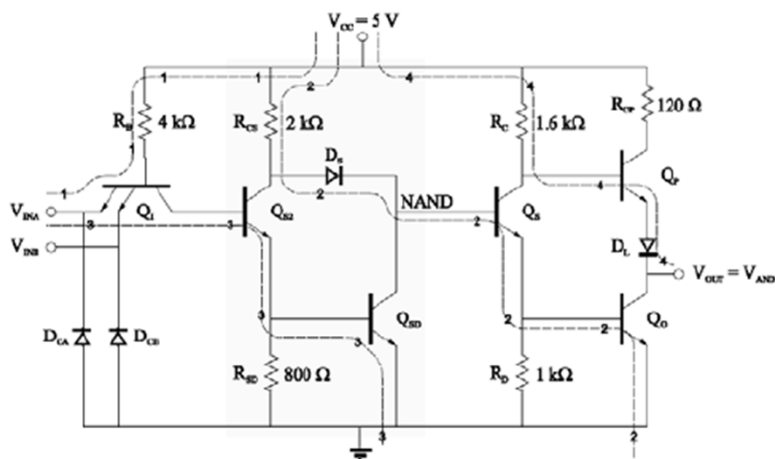


## Chapter 6

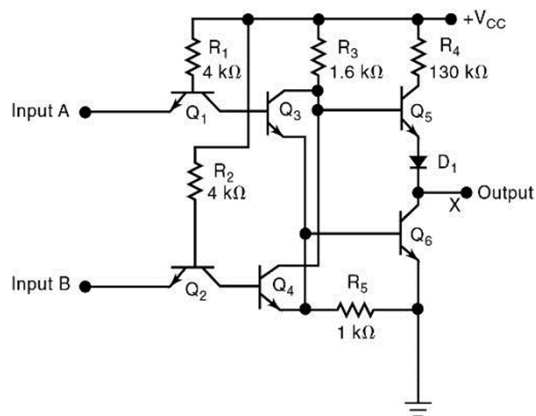
# Bipolar Logic Circuits

Other TTL Gates  
Emitter-Coupled Logic (ECL) and  
Resistor Transistor Logic (RTL)

### TTL AND GATE



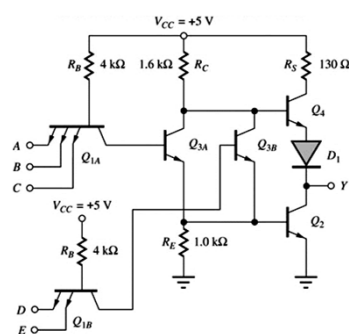
## TTL NOR GATE



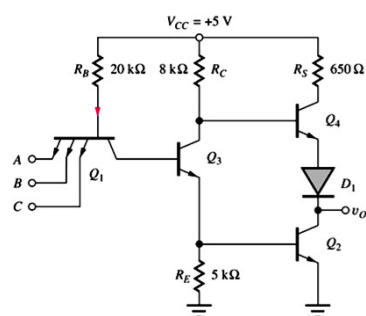
- The **NOR** circuit does *not* use a multiple-emitter transistor.
- Each input is applied to the emitter of a separate transistor.
- The **NOR** circuit uses the same totem-pole arrangement as the **NAND** circuit on the output side

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## Other TTL Gates



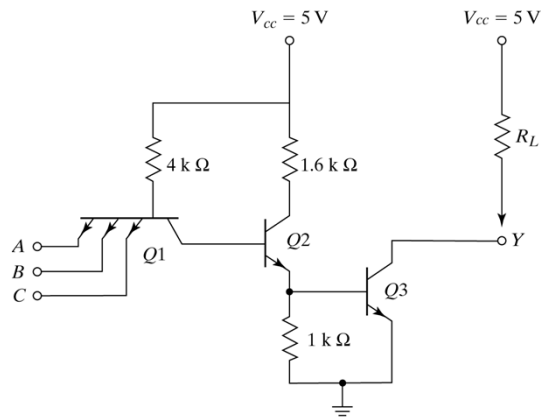
## TTL AND-OR-Invert



## Low-power TTL NAND gate

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## Open-collector TTL Gate



5

## Wired-AND of Two Open-Collector

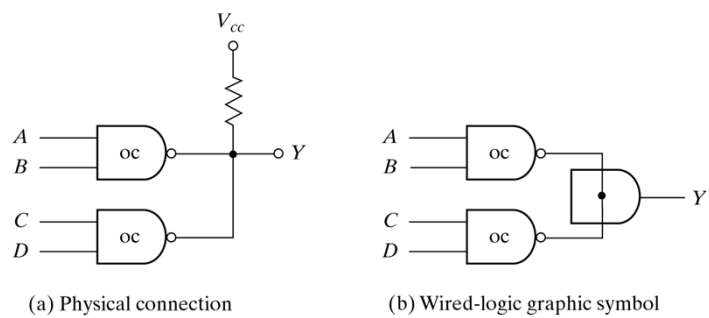


Fig. 10-12 Wired-AND of two Open-Collector (oc) Gates,  $Y = (AB + CD)'$

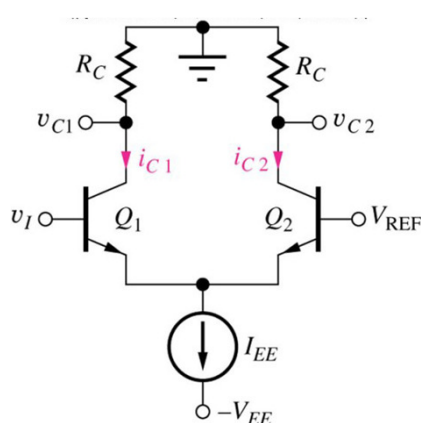
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## Emitter-Coupled Logic (ECL)

- Nonsaturated digital logic family
- Propagation rate as low as 1-2ns
- Used mostly in high speed circuits
- Noise immunity and power dissipation is the worst of all logic families.
- High level -0.8V, Low level -1.8V
- Including
  - Differential input amplifier
  - Internal temperature and voltage compensated bias network
  - Emitter-follower outputs

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## The Current Switch (Emitter-Coupled Pair)

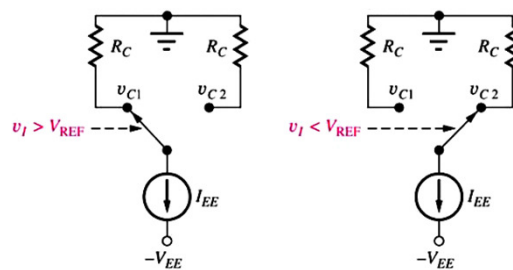


- The building block of emitter-coupled logic (ECL) is the current switch circuit which consists of matched components

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## The Current Switch

- Depending on how much higher or lower the input voltage  $v_I$  is compared to  $V_{REF}$ , the reference current will switch to one of the legs creating a voltage  $v_{C1}$  or  $v_{C2}$ .



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## Mathematical Model for Static Behavior of the Current Switch

- The previous figure showed the ideal case for switching the currents between the two legs, but in real BJTs current will be present in both legs depending upon  $v_{BE}$  of each BJT in the pair
- The collector current difference is given by:

$$i_{C1} - i_{C2} = \alpha_F I_{EE} \tanh\left(\frac{v_{BE1} - v_{BE2}}{2V_T}\right)$$

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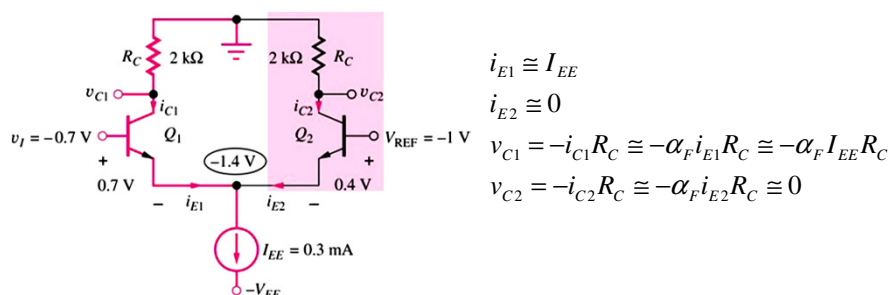
## Typical npn Transistor Parameters

Region	$V_{BE}$ (V)	$V_{CE}$ (V)	Current Relation
Cutoff	< 0.6	Open circuit	$I_B = I_C = 0$
Active	0.6-0.7	> 0.8	$I_C = h_{FE} I_B$
Saturation	0.7-0.8	0.2	$I_B \geq I_C / h_{FE}$

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## Current Switch Analysis for $v_I > V_{REF}$

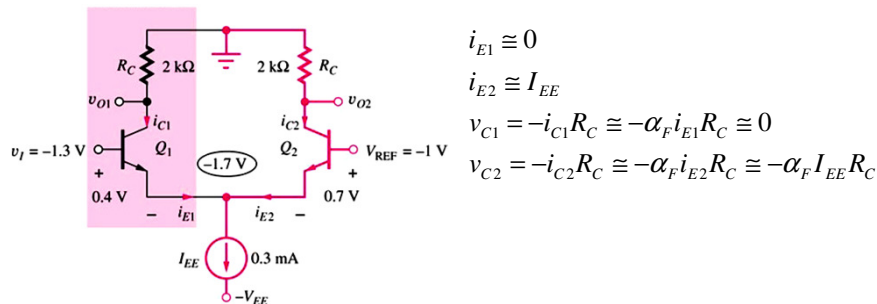
- Given the circuit shown under the given bias conditions ( $v_I$  is 300mV larger than  $V_{REF}$ ), the majority of current will flow in the left leg.



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## Current Switch Analysis for $v_I < V_{REF}$

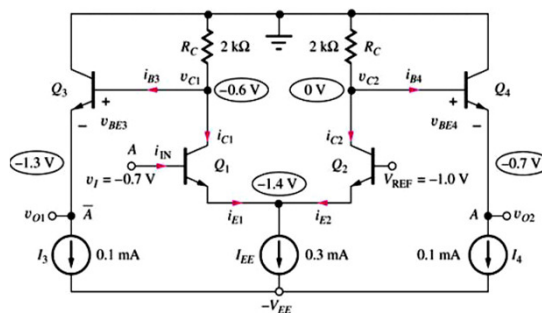
- Given the circuit shown under the given bias conditions ( $v_I$  is 300mV less than  $V_{REF}$ ), the majority of current will flow in the right leg



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## The Emitter-Coupled Logic (ECL) Gate

- The outputs of the previous current switch have the value of either 0V or -0.6V
- The difference of the input and output of the current switch is exactly one base-emitter voltage drop
- For a complete ECL gate, the voltages are shifted by a base-emitter drop as shown in the figure.



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## ECL Gate Summary

$v_I$	$v_{O1}$	$v_{O2}$	$I_{IN}$
$V_{REF} + 0.3V = -0.7V$	-1.3V	-0.7V	+14.3 $\mu$ A
$V_{REF} - 0.3V = -1.3V$	-0.7V	-1.3V	0

$$i_{IN} = i_{B1} = \frac{i_{EE}}{\beta_F + 1} \quad \text{For } v_I = -0.7V$$

$$i_{IN} = 0 \quad \text{For } v_I = -1.3V$$

$$V_{REF} = \frac{V_H + V_L}{2}$$

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## ECL Gate Benefits

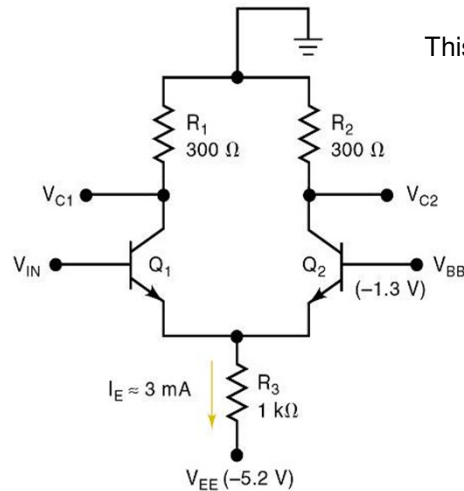
- ECL gates produce both true and complemented outputs
- ECL gates are fast since the BJTs are always in forward active mode, and it only takes a few tenths of a volt to get the output to change states, hence reducing the dynamic power
- ECL gates provide near constant power supply current for all states thereby generating less noise from the other circuits connected to the supply

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## The ECL Digital IC Family

### Basic ECL circuit – differential amplifier



This circuit produces complementary outputs:  $V_{OUT1}$ , equal to  $\overline{V_{IN}}$ , and  $V_{OUT2}$ , equal to  $V_{IN}$ .

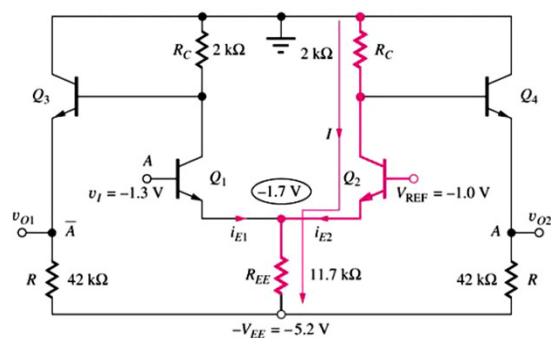
Operating States

$V_{IN}$	Outputs
-1.7 V (logic 0)	$V_{C1} = 0\text{ V}$ $V_{C2} = -0.9\text{ V}$ } $Q_2$ conducts
-0.8 V (logic 1)	$V_{C1} = -0.9\text{ V}$ $V_{C2} = 0\text{ V}$ } $Q_1$ conducts

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## Current Source Implementation

- Instead of using actual current sources for the current biasing in an ECL gate, resistors can be used as shown below

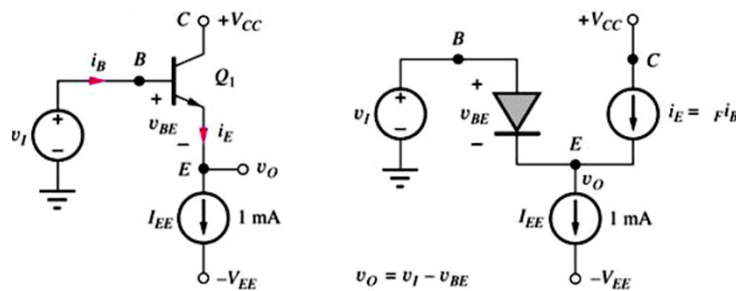


Note that the currents in the emitter-follower legs will not be equal since the output voltages will be different. This will instead be looked at as an average value between the two legs.

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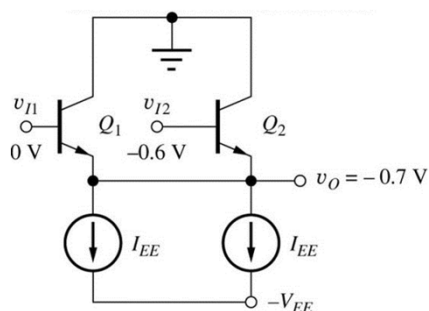
## The Emitter Follower

- The main purpose of the emitter follower in ECL gates is to create a level shift in the output
- The figure shows both the circuit and its transport model for the forward- active region



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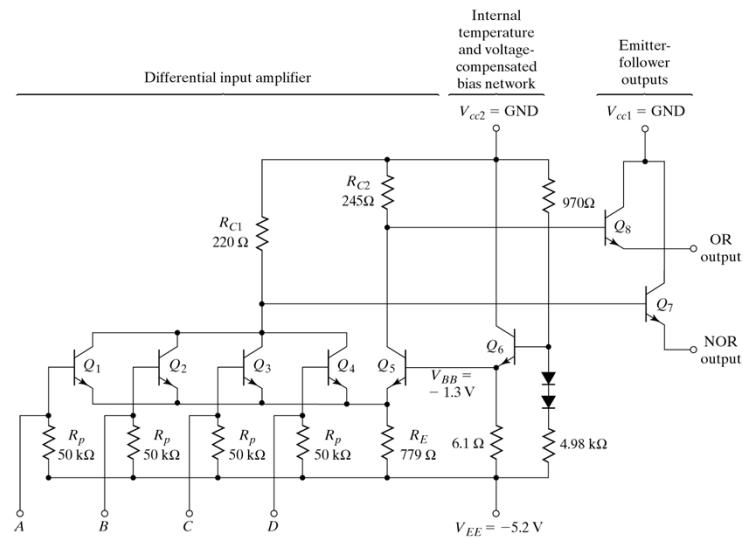
## “Emitter Dotting” or “Wired-OR” Logic



- The circuit shown in the figure exhibits two emitter followers in parallel with a common output
- The result for the shown bias condition implies that  $Q_2$  is cutoff and  $Q_1$  has to handle  $2I_{EE}$

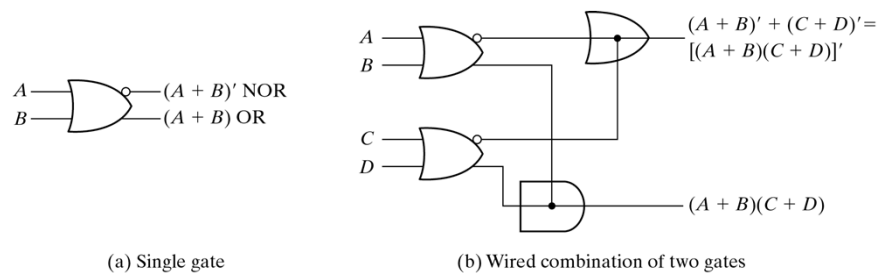
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## ECL Basic OR/NOR Gate



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## Graphic Symbols of ECL Gates



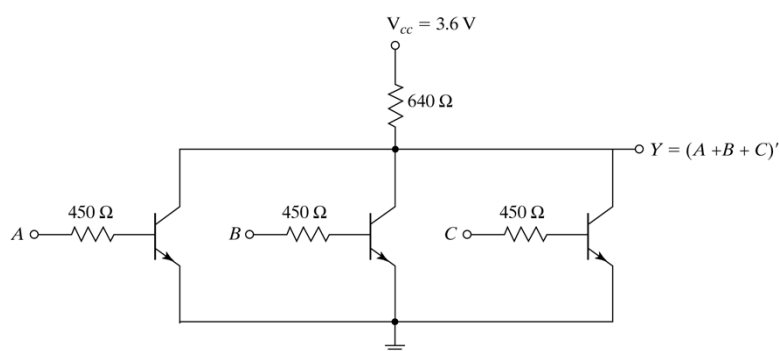
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## ECL characteristics

- Very fast switching with typical propagation delay of 360ps — faster than TTL or CMOS.
- The standard ECL logic levels are nominally -0.8 V and -1.7 V for logical 1 and 0 respectively.
- Worst-case noise margins approximately 150 mV.
- ECL logic gates usually produce an output and its complement, eliminating the need for inverters.
- Current flow remains constant, eliminating noise spikes.

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## RESISTOR-TRANSISTOR LOGIC (RTL)



An RTL NOR Gate with 3 inputs.

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## RTL NOR

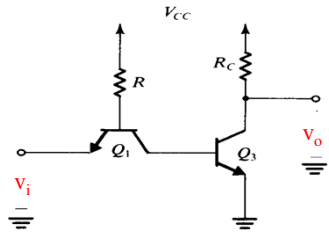
- The 3-input positive NOR gate operates as follows:
- If any input is HIGH, the corresponding transistor is driven into saturation and the output is LOW,  $v_o = V_{CE,sat} \approx 0.2V$ . If all inputs are LOW, then all input transistors are cut off by  $V_\gamma - V(0) = 0.5 - 0.2 = 0.3V$  and the output  $v_o$  is HIGH.
- The value of  $v_o$  depends upon the fan-out. For example, if  $N = 5$ , then the output of the NOR gate is loaded by five  $450\Omega$  resistors in parallel (or  $90\Omega$ ), which is tied to  $V_{BE,sat} \approx 0.8V$ . Under these circumstances (using superposition),
- $$v_o = \frac{3.6 \times 90}{90 + 640} = 1.14V$$
- This voltage must be large enough so that the base current can drive each of the five transistors into saturation. Since
- $$I_B = \frac{1.14 - 0.8V}{0.45k\Omega} = 0.755mA \quad I_C = \frac{3.6 - 0.2V}{0.64k\Omega} = 5.31mA$$

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- then the circuit will operate properly if  $h_{FE} > h_{FEmin} = 5.31/0.76 = 7$ .
- **Resistor-transistor logic uses the minimum space (for a standard digital function) on a silicon wafer, and hence is very economical.**
- **The disadvantages are, low noise immunity, low switching speed and sensitivity to temperature variations.**

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## Simplified TTL vs. RTL

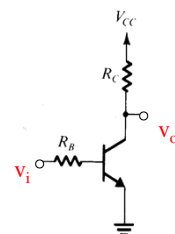


\* Logic levels and noise margins

- Noise Margin for **Low State**
  - $NM_L = V_{IL} - V_O = 0.6 \text{ V} - 0.1 \text{ V} = 0.5 \text{ V}$
- Noise Margin for **High State**
  - $NM_H = V_{OH} - V_{IH} = 5 \text{ V} - 0.7 \text{ V} = 4.3 \text{ V}$
- Unequal noise margins for high and low states.

• Propagation delays

- Output going low  $t_{PHL} = 0.55 \text{ nsec}$
- Output going high  $t_{PLH} = 16 \text{ nsec}$
- Propagation delay  $t_p = 8.3 \text{ nsec}$



\* Logic levels and noise margins

- Noise Margin for **Low State**
  - ★  $NM_L = V_{IL} - V_O = 0.7 \text{ V} - 0.2 \text{ V} = 0.5 \text{ V}$
- Noise Margin for **High State**
  - ★  $NM_H = V_{OH} - V_{IH} = 5 \text{ V} - 0.8 \text{ V} = 4.2 \text{ V}$
- Unequal noise margins for high and low states.

\* Propagation delays

- Output going low  $t_{PHL} = 12 \text{ nsec}$
- Output going high  $t_{PLH} = 100 \text{ nsec}$
- Propagation delay  $t_p = 56 \text{ nsec}$

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